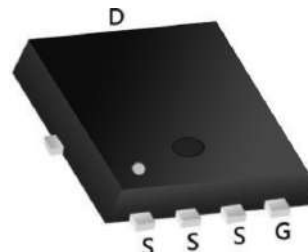


N-Ch 100V Fast Switching MOSFETs

Features:

- ★ 100% EAS Guaranteed
- ★ Green Device Available
- ★ Super Low Gate Charge
- ★ Excellent CdV/dt effect decline
- ★ Advanced high cell density Trench technology

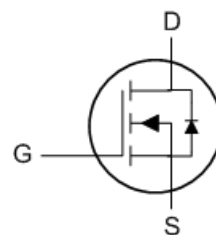


PRPAK5X6 Pin Configuration

Description:

The KWBA0024A is the high cell density trenched N-ch MOSFETs, which provide excellent $R_{DS(on)}$ and gate charge for most of the synchronous buck converter applications.

The KWBA0024A meet the RoHS and Green Product requirement, 100% EAS guaranteed with full function reliability approved.



Product Summary

BVDSS	$R_{DS(on)}$	I_D
100V	10m Ω	104A

Absolute Maximum Ratings

Symbol	Parameter	Rating	Units
V_{DS}	Drain-Source Voltage	100	V
V_{GS}	Gate-Source Voltage	± 20	V
$I_D @ T_C = 25^\circ C$	Continuous Drain Current, $V_{GS} @ 10V^{1,6}$	104	A
$I_D @ T_C = 100^\circ C$	Continuous Drain Current, $V_{GS} @ 10V^{1,6}$	66	A
I_{DM}	Pulsed Drain Current ²	200	A
EAS	Single Pulse Avalanche Energy ³	180	mJ
I_{AS}	Avalanche Current	60	A
$P_D @ T_C = 25^\circ C$	Total Power Dissipation ⁴	156	W
T_{STG}	Storage Temperature Range	-55 to 150	$^\circ C$
T_J	Operating Junction Temperature Range	-55 to 150	$^\circ C$

Thermal Data

Symbol	Parameter	Typ.	Max.	Unit
$R_{\theta JA}$	Thermal Resistance Junction-Ambient ¹	---	62	$^\circ C/W$
$R_{\theta JC}$	Thermal Resistance Junction-Case ¹	---	0.8	$^\circ C/W$

Electrical Characteristics ($T_J=25\text{ }^{\circ}\text{C}$, unless otherwise noted)

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
BV_{DSS}	Drain-Source Breakdown Voltage	$V_{GS}=0V$, $I_D=250\mu A$	100	---	---	V
$R_{DS(ON)}$	Static Drain-Source On-Resistance ²	$V_{GS}=10V$, $I_D=15A$	---	8.5	10	m Ω
$V_{GS(th)}$	Gate Threshold Voltage	$V_{GS}=V_{DS}$, $I_D=250\mu A$	2.5	---	4.5	V
I_{DSS}	Drain-Source Leakage Current	$V_{DS}=80V$, $V_{GS}=0V$, $T_J=25^{\circ}\text{C}$	---	---	1	μA
		$V_{DS}=80V$, $V_{GS}=0V$, $T_J=55^{\circ}\text{C}$	---	---	5	
I_{GSS}	Gate-Source Leakage Current	$V_{GS}=\pm 20V$, $V_{DS}=0V$	---	---	± 100	nA
gfs	Forward Transconductance	$V_{DS}=5V$, $I_D=30A$	---	50	---	S
R_g	Gate Resistance	$V_{DS}=0V$, $V_{GS}=0V$, $f=1\text{MHz}$	---	1.2	---	Ω
Qg	Total Gate Charge (10V)	$V_{DS}=80V$, $V_{GS}=10V$, $I_D=30A$	---	84	---	nC
Qgs	Gate-Source Charge		---	28	---	
Qgd	Gate-Drain Charge		---	26	---	
Td(on)	Turn-On Delay Time	$V_{DD}=40V$, $V_{GS}=10V$, $R_G=3.3\Omega$, $I_D=30A$	---	36	---	ns
Tr	Rise Time		---	71	---	
Td(off)	Turn-Off Delay Time		---	50	---	
Tf	Fall Time		---	23	---	
Ciss	Input Capacitance	$V_{DS}=15V$, $V_{GS}=0V$, $f=1\text{MHz}$	---	5580	---	pF
Coss	Output Capacitance		---	571	---	
Crss	Reverse Transfer Capacitance		---	278	---	

Diode Characteristics

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
I_S	Continuous Source Current ^{1,5}	$V_G=V_D=0V$, Force Current	---	---	104	A
I_{SM}	Pulsed Source Current ^{2,5}		---	---	200	A
V_{SD}	Diode Forward Voltage ²	$V_{GS}=0V$, $I_S=A$, $T_J=25^{\circ}\text{C}$	---	---	1.2	V
t_{rr}	Reverse Recovery Time	$I_F=30A$, $dI/dt=100A/\mu s$, $T_J=25^{\circ}\text{C}$	---	24	---	nS
Q_{rr}	Reverse Recovery Charge		---	28	---	nC

Note :

- 1.The data tested by surface mounted on a 1 inch² FR-4 board with 2OZ copper.
- 2.The data tested by pulsed , pulse width $\leq 300\mu s$, duty cycle $\leq 2\%$
- 3.The EAS data shows Max. rating . The test condition is $V_{DD}=25V$, $V_{GS}=10V$, $L=0.1mH$, $I_{AS}=60A$
- 4.The power dissipation is limited by 150°C junction temperature
- 5.The data is theoretically the same as I_D and I_{DM} , in real applications , should be limited by total power dissipation.
- 6.Package limitation current is 90A.

Typical Characteristics

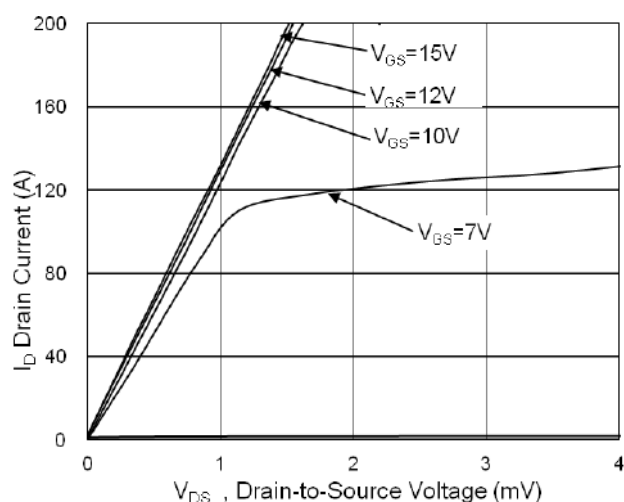


Fig.1 Typical Output Characteristics

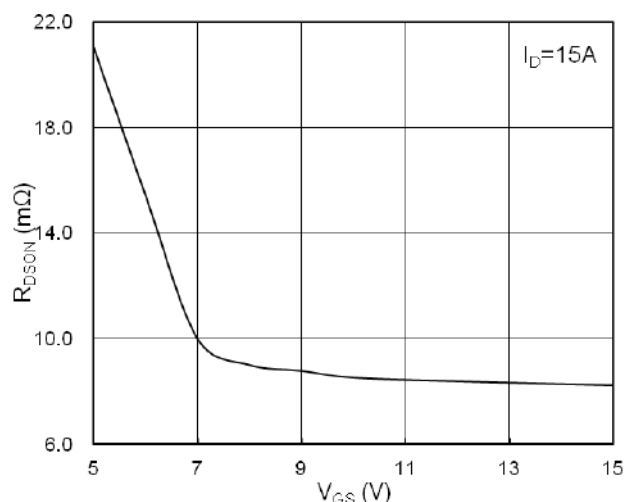


Fig.2 On-Resistance v.s Gate-Source

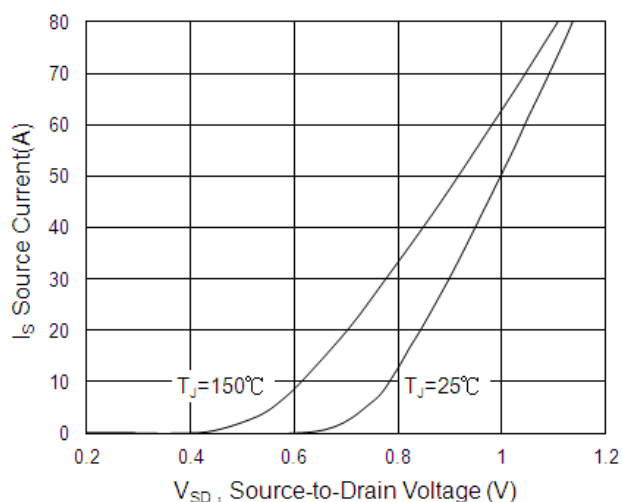


Fig.3 Forward Characteristics of Reverse

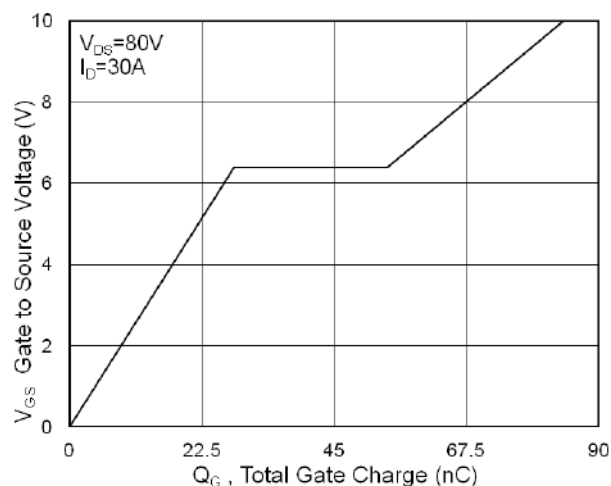


Fig.4 Gate-Charge Characteristics

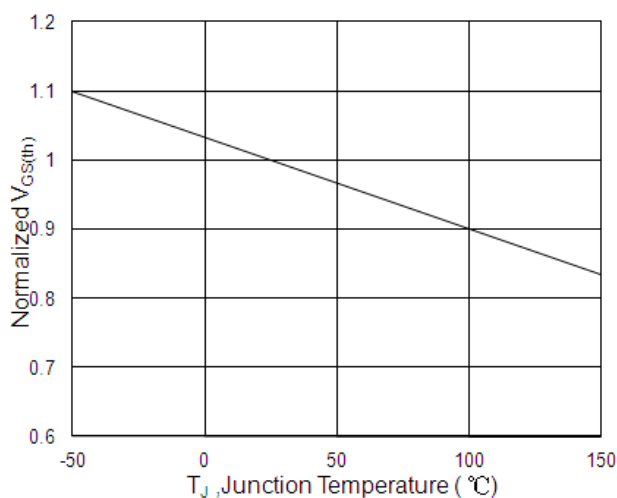


Fig.5 Normalized $V_{GS(th)}$ vs. T_J

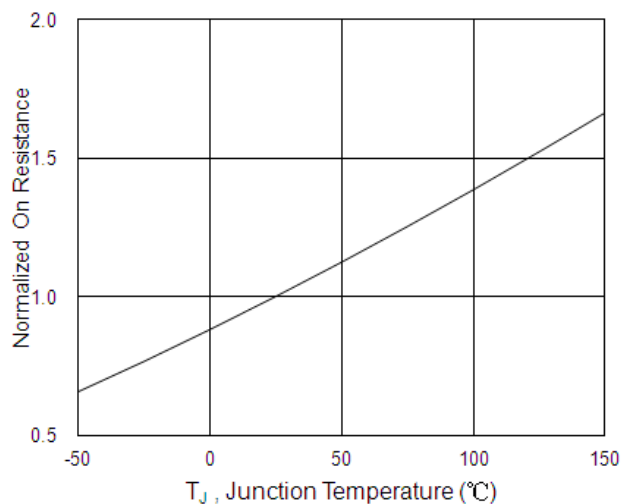


Fig.6 Normalized $R_{DS(on)}$ vs. T_J

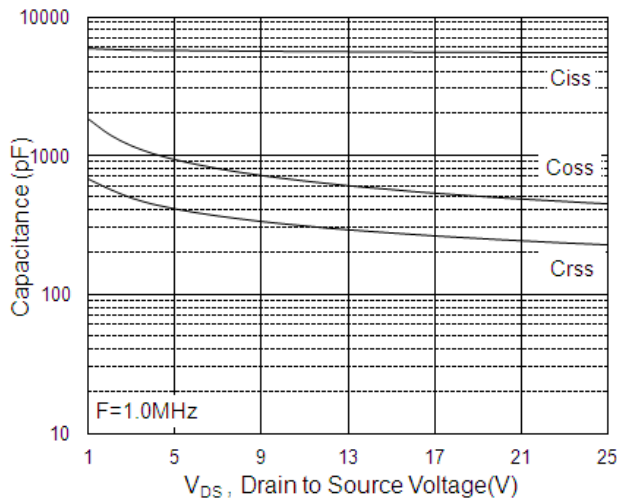


Fig.7 Capacitance

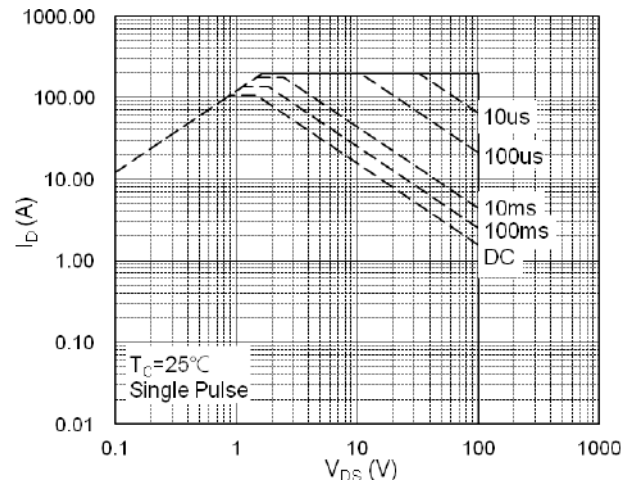


Fig.8 Safe Operating Area

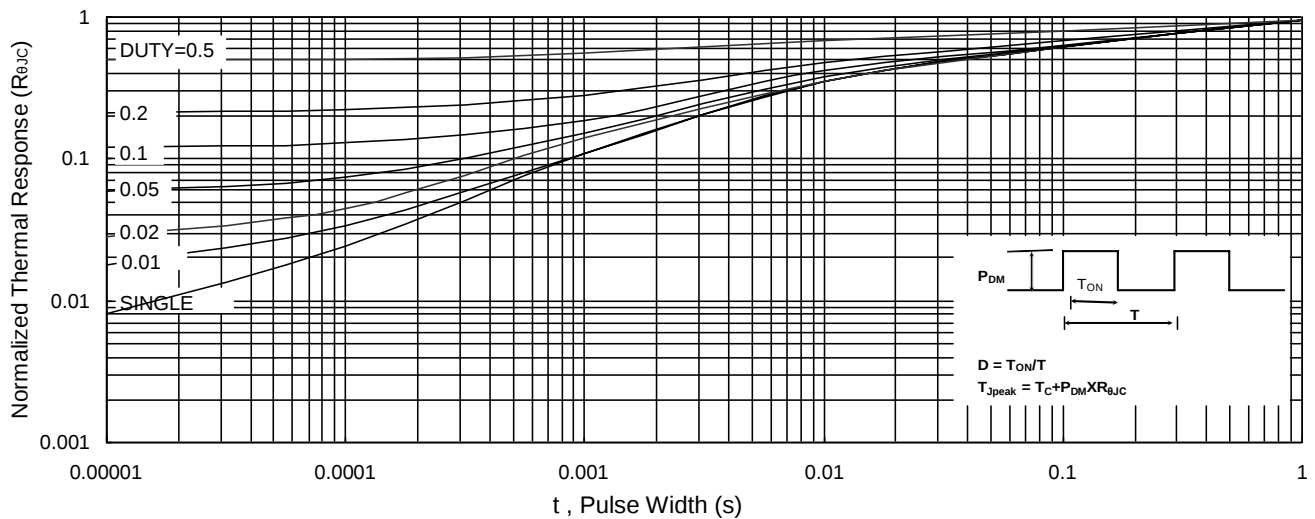


Fig.9 Normalized Maximum Transient Thermal Impedance

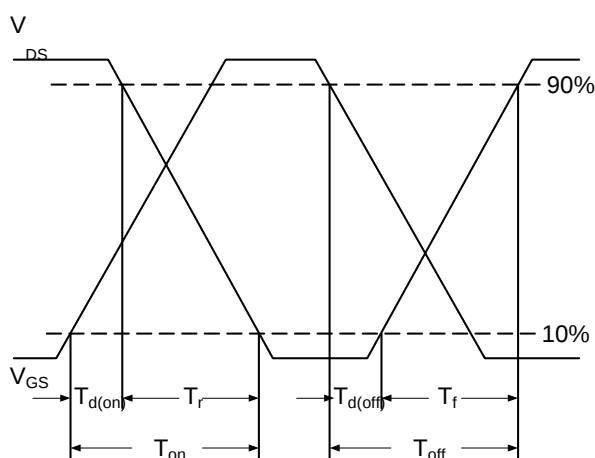


Fig.10 Switching Time Waveform

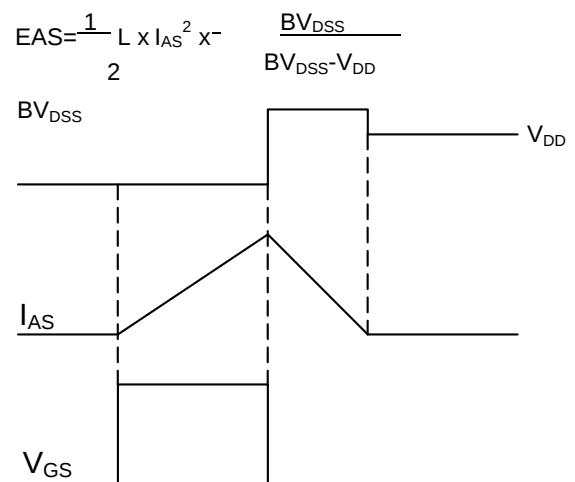


Fig.11 Unclamped Inductive Switching Waveform